TOSHIBA PHOTOCOUPLER

TLP620(D4)SERIES, TLP621(D4)SERIES, TLP750(D4)SERIES

ATTACHMENT: SPECIFICATIONS FOR VDE0884 OPTION: (D4)

Types: TLP620, TLP620-2, TLP620-3, TLP620-4, TLP621, TLP621-2, TLP621-3, TLP621-4, TLP750,

TLP751

Type designations for 'Option: (D4)', which are tested under VDE0884 requirements.

: TLP621 (D4-GR-LF2) VDE0884 option

> CTR rank GR

standard lead bend LF2

Use Toshiba standard type number for safety standard application. Note:

Ex. TLP621 (D4-GR-LF2) \rightarrow TLP621

VDE0884 ISOLATION CHARACTERISTICS

DESCRIPTION	SYMBOL	RATING	UNIT
Application Classification	/ WV		
(DIN VDE0109/12.83, Table 1) for rated mains voltage≤300V _{rms}			
for rated mains voltage≦300V _{rms}		I-IV	
for rated mains voltage≤600V _{rms}		I-III	
Climatic Classification		55 / 100 / 21	
(DIN IEC68 Teil 1/09.80)		55/100/21	
Pollution Degree (DIN VDE0109/12.83)		2	_
Maximum Operating Insulation Voltage	V _{IORM}	890	Vpk
Input to output Test Voltage, Method A			ALM NO
Vpr=1.5×V _{IORM} , Type and Sample Test	Vpr	1335	Vpk
tp=60s, Partial Discharge<5pC	100 M/P		
Input to output Test Voltage, Method B			
Vpr=1.875×V _{IORM} , 100% Production Test	Vpr	1670	Vpk
tp=1s, Partial Discharge < 5pC			
Highest Permissible Overvoltage	77	8000	Vpk
(Transient Overvoltage, t _{pr} =10s)	V_{TR}		
Safety Limiting Values (Max. permissible ratings in			
case of fault, also refer to thermal derating curve)			-ca1
Current (Input current IF, Psi=0)	I _{si}	300	mA
Power (Output or Total Power Dissipation)	P _{si}	500	mW
Temperature	T_{si}	150	°C
Insulation Resistance at Tsi, V _{IO} =500V	R _{si}	\geq 10^{9}	Ω

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INSULATION RELATED SPECIFICATIONS

Minimum Creepage Distance (*)	Cr	6.4mm	
Minimum Clearance (*)	Cl	6.4mm	
Minimum Insulation Thickness	ti	$0.4 \mathrm{mm}$	
Comperative Tracking Index	CTI	175	
(DIN IEC112/VDE0303, Part 1)	011	(VDE0109/12.83 Group Ⅲ a)	

- ((*) in accordance with DIN VDE0109/12.83, Table 2, & 4)
 - (*1) If a printed circuit is incorporated, the creepage distance and clearance may be reduced below this value (e. g. at a standard distance between soldering eye centres of 7.5mm). If this is not permissible, the user shall take suitable measures.
 - (*2) This photocoupler is suitable for 'safe electrical isolation' only within the safety limit data.

Maintenance of the safety data shall be ensured by means of protective circuits.

TLP620, 620-2, 620-3, 620-4 TLP621, 621-2, 621-3, 621-4

TLP750, 751

VDE Test sign: Marking on product

for VDE0884

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Marking on packing for VDE0884

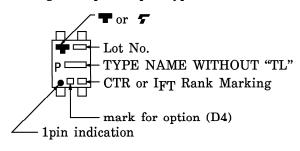


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Marking Example: 4 pin Type



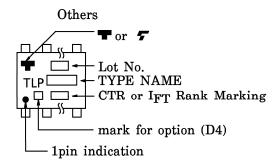


Figure 1 Partial discharge measurement procedure according to VDE0884 Destructive test for qualification and sampling tests.

Method A

(for type and sampling tests, destructive tests)

$$\begin{array}{lll} t_1, \, t_2 & = 1 \,\, \text{to} \,\, 10s \\ t_3, \, t_4 & = 1s \\ t_P \, (\text{Measuring time for} \\ & \text{partial discharge}) \,\, = 50s \\ t_b & = 62s \\ t_{\text{ini}} & = 10s \end{array}$$

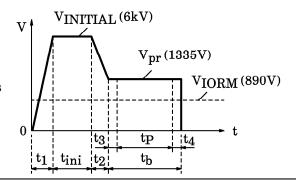


Figure 2 Partial discharge measurement procedure according to VDE0884 Non-destructive test for 100% inspection.

Method B

(for sample test, non-destructive test)

$$\begin{array}{ll} t_3,\ t_4 &= 0.1s \\ t_P \ (\text{Measuring time for} \\ & \text{partial discharge)} &= 1s \\ t_b &= 1.2s \end{array}$$

